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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Chan, et al.

Serial No.: 09/817,120

Group Art Unit: 2825

Filed: March 27, 2001

Examiner: R. Rocchegiani

For: METHOD FOR MANUFACTURING DEVICE SUBSTRATE WITH METAL
BACK-GATE AND STRUCTURE FORMED THEREBY

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

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TECHNOLOGY CENTER 2800

EXCESS CLAIM FEE PAYMENT LETTER

Sir:

Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below.

	<u>AFTER AMENDMENT</u>	<u>PREV. PAID FOR</u>	<u>EXTRA CLAIMS PRESENT</u>	<u>RATE</u>	<u>FEE DUE</u>
Indep. Claims	5 -	4	= 1	x \$84.00	\$ 84.00
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$ 84.00

Please charge Assignee's Deposit Account No. 50-0510 the amount of \$84.00 to cover the excess claim fees. A duplicate copy of this sheet is enclosed.

The Commissioner is authorized charge any deficiencies in fees and credit any overpayment of fees to Assignee's Deposit Account No. 50-0510.

Respectfully Submitted,

Date:

3/4/04

Sean M. McGinn
Reg. No. 34,386

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AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated December 4, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 22-35 without prejudice or disclaimer.

2. (Amended) The method of claim 1, wherein said intermediate gluing layer comprises one of a-Si, Si₃N₄ and a combined layer of a-Si and Si₃N₄.

4. (Amended) The method of claim 3, wherein said depositing of said W comprises a physical vapor deposition (PVD) of W.

6. (Amended) A method of forming a semiconductor substrate, comprising:
forming a metal back-gate over a substrate;
forming a passivation layer on the metal back-gate to prevent the metal back-gate from reacting with radical species; and
providing an intermediate gluing layer on said passivation layer to enhance adhesion between said metal back-gate and said substrate,
wherein said forming of said metal back-gate comprises:

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